N-CHANNEL MOS FIELD EFFECT POWER TRANSISTOR

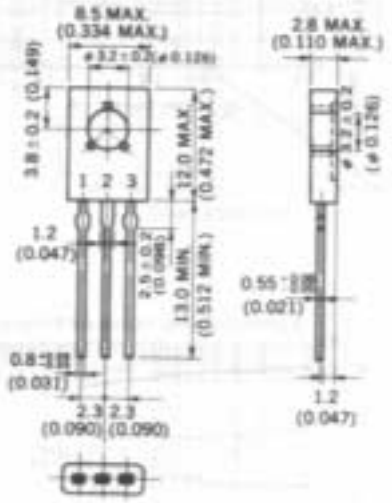
2SK701

DESCRIPTION The 2SK701 is N-Channel MOS Field Effect Power Transistor designed for solenoid, motor and lamp driver.

FEATURES

- 4 V Gate Drive – Logic level –
- Low $R_{DS(on)}$
- No Second Breakdown

PACKAGE DIMENSIONS
in millimeters (inches)



1. Source
2. Drain connected to mounting plane
3. Gate

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

- Storage Temperature . . . . . −55 to +150 °C
- Junction Temperature . . . . . 150 °C Maximum

Maximum Power Dissipations

- Total Power Dissipation . . . . . 1.3 W
- Total Power Dissipation (T_C = 25 °C) . . . . . 15 W

Maximum Voltages and Currents (T_a = 25 °C)

V_{DSS}	Drain to Source Voltage	60	V
V_{GSS}	Gate to Source Voltage.	±20	V
$I_{D(DC)}$	Drain Current (DC)	±2	A
$I_{D(pulse)}$	Drain Current (pulse)*	±6	A

* PW ≤ 300 μs, Duty Cycle ≤ 10 %

ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
$R_{DS(on)}$	Drain to Source On-State Resistance		0.4	0.6	Ω	V_{GS} = 10 V, I_D = 1 A
$R_{DS(on)}$	Drain to Source On-State Resistance		0.6	0.85	Ω	V_{GS} = 4 V, I_D = 1 A
$V_{GS(off)}$	Gate to Source Cutoff Voltage	1.0		2.5	V	V_{DS} = 10 V, I_D = 1 mA
$\|Y_{fs}\|$	Forward Transfer Admittance	0.5			S	V_{DS} = 10 V, I_D = 1 A
I_{DSS}	Drain Leakage Current			10	μA	V_{DS} = 60 V, V_{GS} = 0
I_{GSS}	Gate to Source Leakage Current			±100	nA	V_{GS} = ±20 V, V_{DS} = 0
C_{iss}	Input Capacitance		200		pF	V_{DS} = 10 V V_{GS} = 0 f = 1 MHz
C_{oss}	Output Capacitance		70		pF	
C_{rss}	Reverse Transfer Capacitance		15		pF	
$t_{d(on)}$	Turn-On Delay Time		45		ns	I_D = 1 A, V_{CC} ≈ 50 V R_L = 50 Ω R_{in} = 10 Ω
t_r	Rise Time		40		ns	
$t_{d(off)}$	Turn-Off Delay Time		450		ns	
t_f	Fall Time		110		ns	